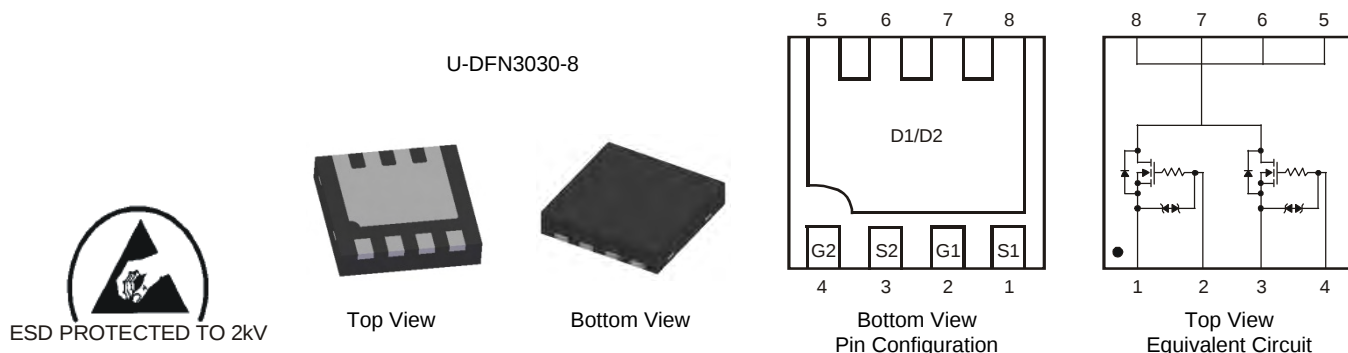


DUAL N-CHANNEL ENHANCEMENT MODE MOSFET
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 2KV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

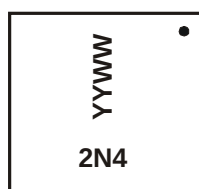
Mechanical Data

- Case: U-DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208 ^(e4)
- Polarity: See Diagram
- Weight: 0.0172 grams (approximate)


Ordering Information (Note 4)

Part Number	Case	Packaging
DMG8601UFG-7	U-DFN3030-8	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


2N4 = Product marking code
 YYWW = Date code marking
 YY = Last digit of year (ex: 09 for 2009)
 WW = Week code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C	I _D	6.1	A
		T _A = +70°C		5.2	
Pulsed Drain Current			I _{DM}	27	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.92	W
Thermal Resistance, Junction to Ambient @T _A = +25°C	R _{θJA}	136	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
Gate-Source Breakdown Voltage	BV _{SGS}	±12	-	-	V	V _{DS} = 0V, I _G = ±250μA
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.35	-	1.05	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	17	23	mΩ	V _{GS} = 4.5V, I _D = 6.5A
		-	20	27		V _{GS} = 2.5V, I _D = 5.5A
		-	25	34		V _{GS} = 1.8V, I _D = 3.5A
		-	-	-		V _{GS} = 1.8V, I _D = 3.5A
Forward Transfer Admittance	Y _{fs}	-	10	-	S	V _{DS} = 10V, I _D = 5A
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	-	143	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	74	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	29	-	pF	
Gate Resistance	R _g	-	202	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	8.8	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A
Gate-Source Charge	Q _{gs}	-	1.4	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.0	-	nC	
Turn-On Delay Time	t _{D(on)}	-	53	-	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 10Ω, R _G = 6Ω
Turn-On Rise Time	t _r	-	78	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	562	-	ns	
Turn-Off Fall Time	t _f	-	234	-	ns	

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
6. Short duration pulse test used to minimize self-heating effect.

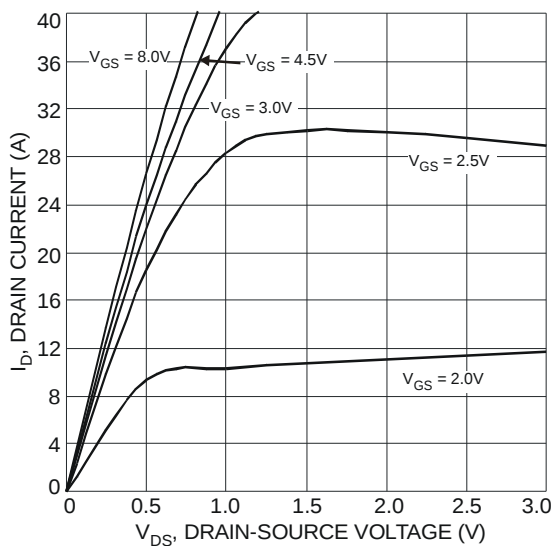


Fig. 1 Typical Output Characteristic

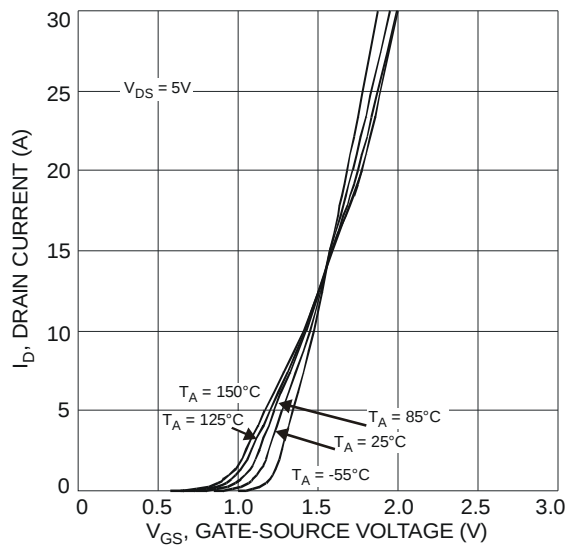


Fig. 2 Typical Transfer Characteristic

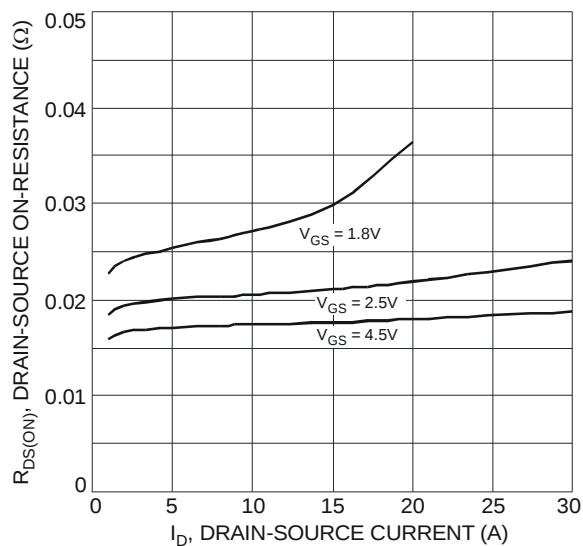


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

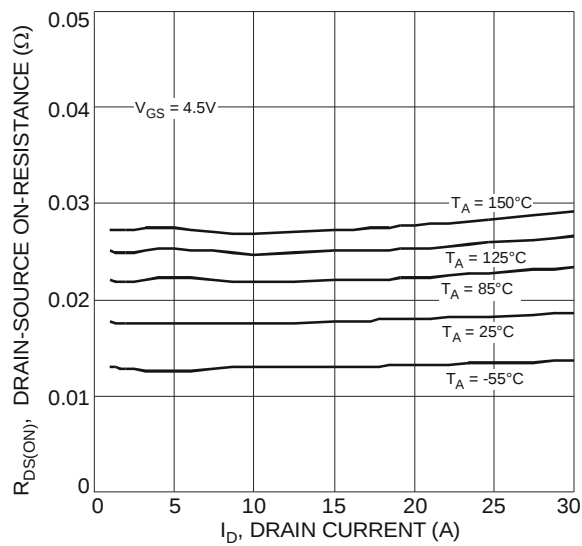


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

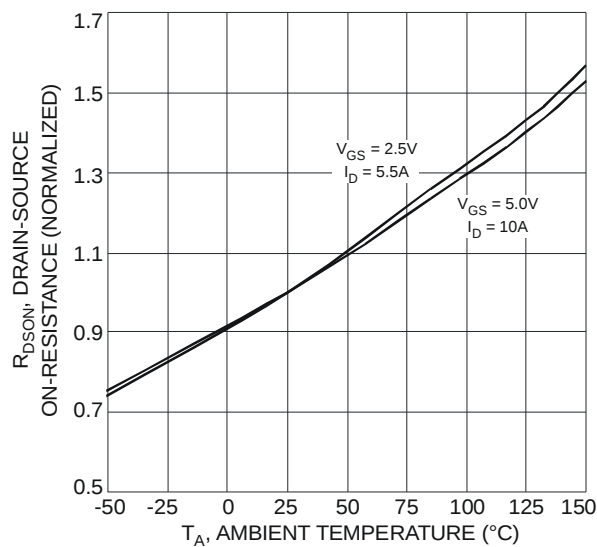


Fig. 5 On-Resistance Variation with Temperature

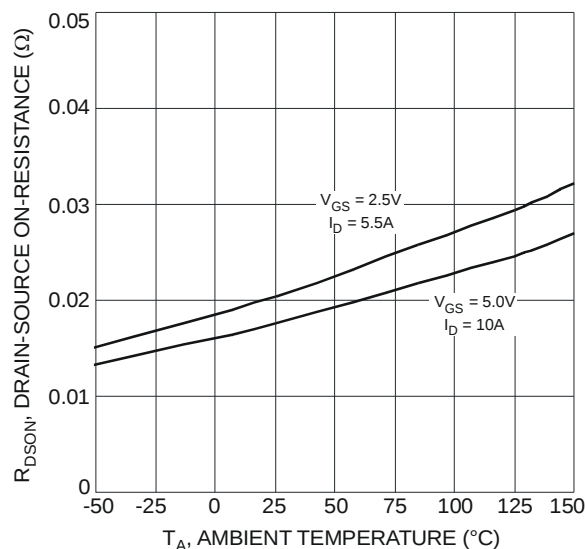


Fig. 6 On-Resistance Variation with Temperature

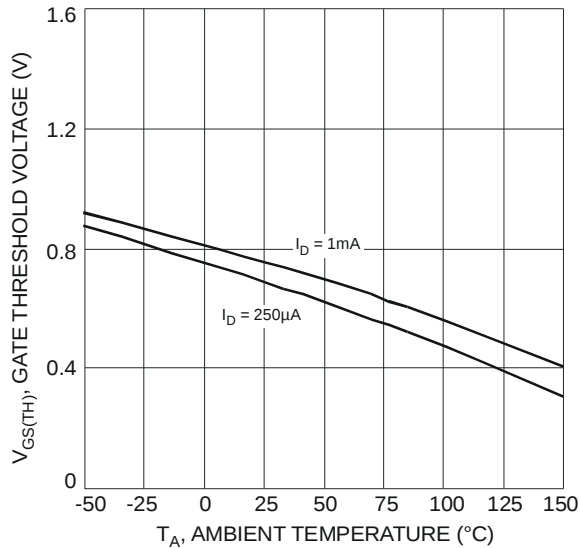


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

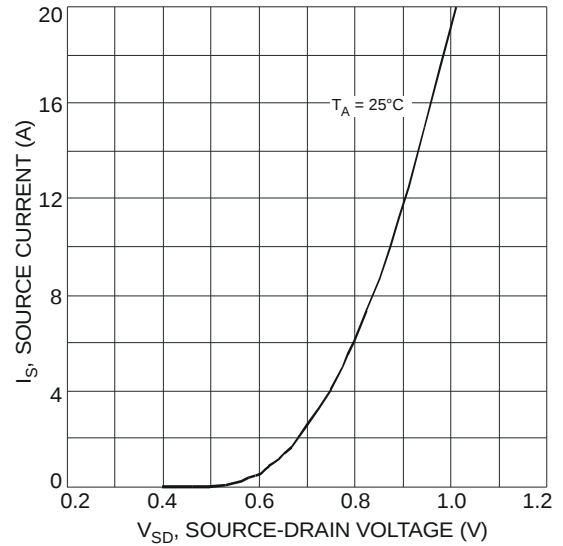


Fig. 8 Diode Forward Voltage vs. Current

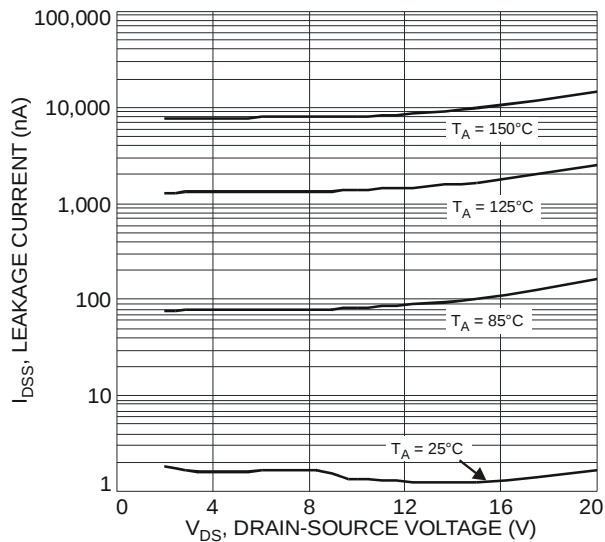


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage

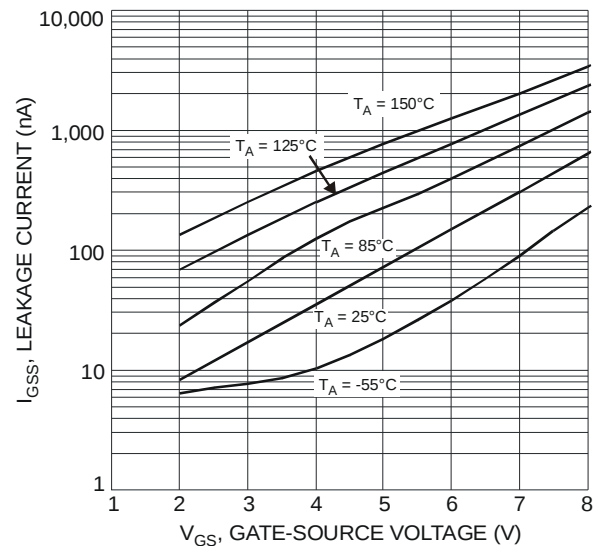


Fig. 10 Gate-Source Leakage Current vs. Voltage

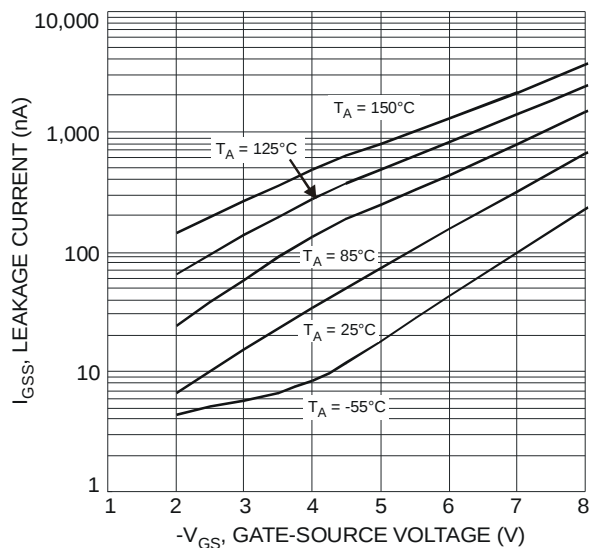


Fig. 11 Gate-Source Leakage Current vs. Voltage

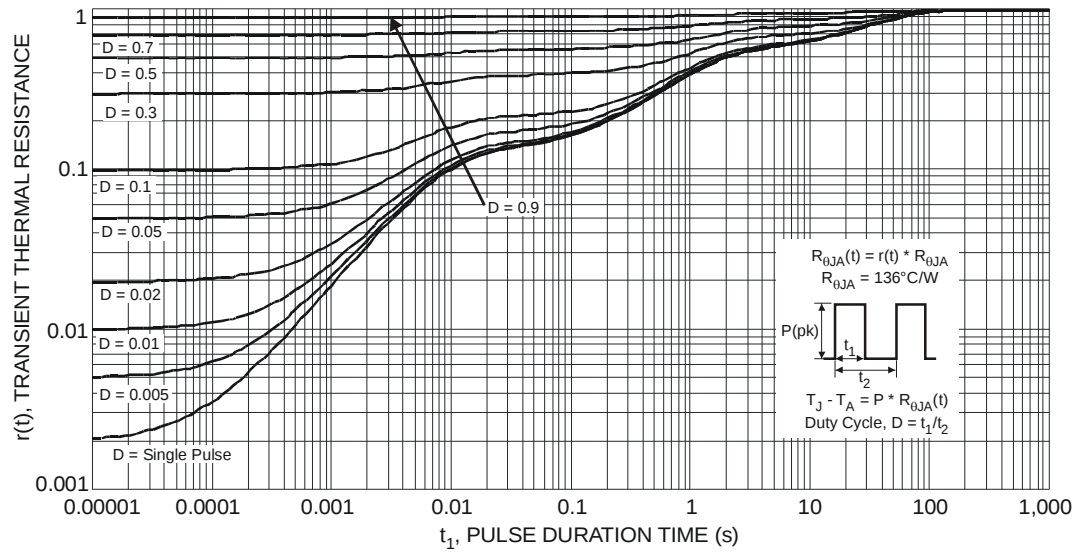
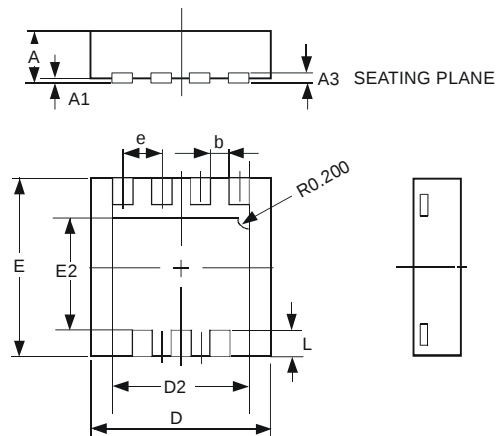


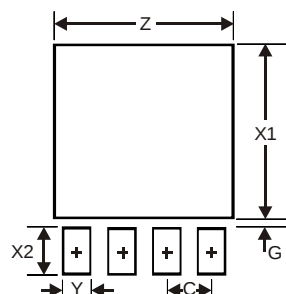
Fig. 12 Transient Thermal Response

Package Outline Dimensions

 Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.


U-DFN3030-8			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.02
A3	—	—	0.15
b	0.29	0.39	0.34
D	2.90	3.10	3.00
D2	2.19	2.39	2.29
e	—	—	0.65
E	2.90	3.10	3.00
E2	1.64	1.84	1.74
L	0.30	0.60	0.45
All Dimensions in mm			

Suggested Pad Layout

 Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.


Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Y	0.39
C	0.65

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